imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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SEMICONDUCTOR

MPSA43

NPN High Voltage Amplifier

- This device is designed for application as a video output to drive color CRT and other high voltage applications.
- Sourced from process 48.
- · See MPSA42 for characteristics.



1. Emitter 2. Base 3. Collector

Absolute Maximum Ratings * TA=25°C unless otherwise noted

Symbol	Parameter	Value	Units
/ _{CES}	Collector-Emitter Voltage	200	V
V _{CBO}	Collector-Base Voltage	200	V
V _{EBO}	Emitter-Base Voltage	6.0	V
I _C	Collector Current - Continuous	200	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 ~ +150	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

These ratings are based on a maximum junction temperature of 150 degrees C.
These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics TA=25°C unless otherwise noted

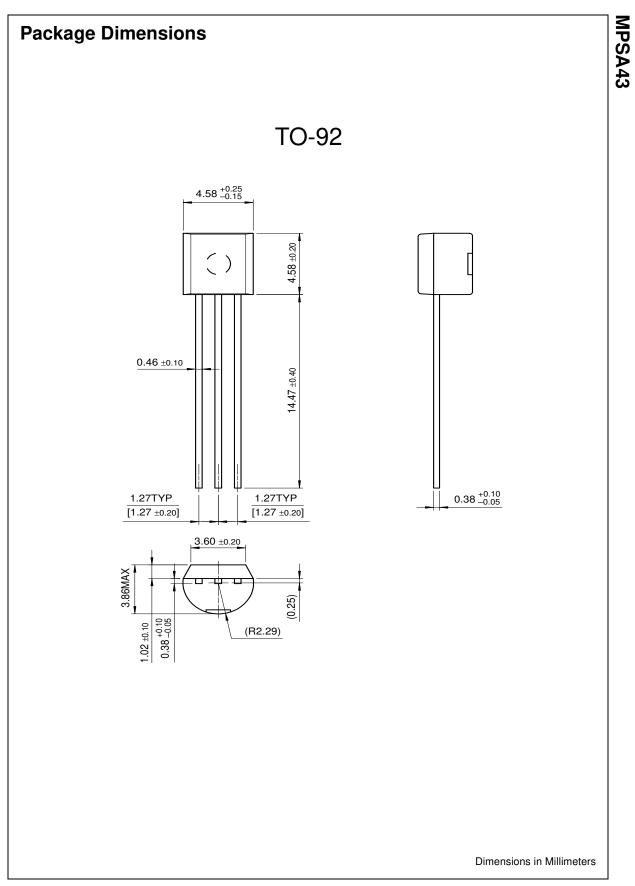
Symbol	Parameter	Test Condition	Min.	Max.	Units			
Off Characteristics								
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage *	$I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0$	200		V			
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{C} = 100 \mu A, I_{E} = 0$	200		V			
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm C} = 100 \mu {\rm A}, \ I_{\rm C} = 0$	6.0		V			
I _{CBO}	Collector Cutoff Current	$V_{CB} = 160V, I_E = 0$		0.1	μA			
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 4.0V, I_{C} = 0$		0.1	μA			
On Characteristics *								
h _{FE}	DC Current Gain	I _C = 1.0mA, V _{CE} = 10V	25					
		$I_{C} = 10 \text{mA}, V_{CE} = 10 \text{V}$	40					
		$I_{C} = 30 \text{mA}, V_{CE} = 10 \text{V}$	50	200				
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_{\rm C} = 20 {\rm mA}, I_{\rm B} = 2.0 {\rm mA}$		0.4	V			
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_{\rm C} = 20 {\rm mA}, I_{\rm B} = 2.0 {\rm mA}$		0.9	V			
Small Sigr	nal Characteristics *			•	•			
f _T	Current Gain Dandwidth Product	I _C = 10mA, V _{CE} = 20V, f = 100MHz	50		MHz			
C _{cb}	Collector-Base Capacitance	$V_{CB} = 20V, I_{F} = 0, f = 1.0MHz$		4.0	pF			

* Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2.0%

Thermal Characteristics $T_A=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Max.	Units
PD	Total Device Dissipation	625	mW
-	Derate above 25°C	5.0	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	200	°C/W

MPSA43



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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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